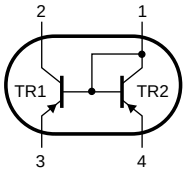
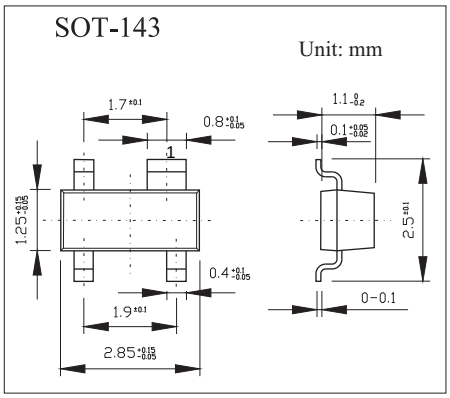
# PNP general purpose double transistor
# BCV62

## ■ Features

- High current gain
- Low collector-emitter saturation voltage




## ■ Absolute Maximum Ratings Ta = 25℃

| Parameter | Symbol | Rating | Unit |
|---|---|---|---|
| Collector-base voltage | $V_{CBO}$ | -30 | V |
| Collector-emitter voltage | $V_{CEO}$ | -30 | V |
| Emitter-base voltage | $V_{EBO}$ | -6 | V |
| Collector current | $I_C$ | -100 | mA |
| Power dissipation | $P_D$ | 250 | mW |
| Thermal resistance from junction to ambient | $R_{\theta JA}$ | 500 | ℃/W |
| Operating and Storage and Temperature Range | $T_j$, $T_{STG}$ | -55 to +150 | ℃ |

# BCV62

## ■ Electrical Characteristics Ta = 25℃

| Parameter | Symbol | Test conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| Transistor TR1 | | | | | | |
| Collector-Base Breakdown Voltage | $V_{(BR)CBO}$ | $I_C$ = -10 μA, $I_E$ = 0 | -30 | | | V |
| Collector-Emitter Breakdown Voltage | $V_{(BR)CEO}$ | $I_C$ = -10 mA, $I_B$ = 0 | -30 | | | V |
| Emitter-Base Breakdown Voltage | $V_{(BR)EBO}$ | $I_C$ = -10 μA, $I_C$ = 0 | -6 | | | V |
| Collector cutoff current | $I_{CBO}$ | $V_{CB}$=-30V, $I_E$=0 | | | -15 | nA |
| Emitter cutoff current | $I_{EBO}$ | $V_{EB}$=-5V, $I_C$=0 | | | -100 | nA |
| DC current gain | $h_{FE}$ | $V_{CE}$=-5V, $I_C$= -100μA | 100 | | | |
| | | $V_{CE}$=-5V, $I_C$=-2mA | 100 | | 800 | |
| collector-emitter saturation voltage * | $V_{CE(sat)}$ | $I_C$ = -10 mA; $I_B$ = -0.5 mA | | | -0.3 | V |
| | | $I_C$ = -100 mA; $I_B$ = -5 mA | | | -0.65 | V |
| base-emitter saturation voltage * | $V_{BE(sat)}$ | $I_C$ = -10 mA; $I_B$ = -0.5 mA | | -0.7 | | V |
| | | $I_C$ = -100 mA; $I_B$ = -5 mA | | -0.85 | | V |
| Collector capacitance | $C_c$ | $I_E$ = $i_e$ = 0; $V_{CB}$ = -10 V; f = 1 MHz | | 4.5 | | pF |
| Transition frequency | $f_T$ | $I_C$ = -10 mA; $V_{CE}$ = -5 V; f = 100 MHz | 100 | | | MHz |
| Noise figure | F | $I_C$ =-200μA; $V_{CE}$ =-5 V; $R_S$ =2kΩ; f = 1 kHz; B = 200 Hz | | | 10 | dB |
| Transistor TR2 | | | | | | |
| Base-emitter forward voltage | $V_{EBS}$ | $V_{CB}$ = 0; $I_E$ = 250 mA | | | 1.5 | V |
| | | $V_{CB}$ = 0; $I_E$ = 10μA | 0.4 | | | mV |
| DC current gain | $h_{FE}$ | $I_C$ = -2 mA; $V_{CE}$ = -5 V | | | | |
| BCV62A | | | 125 | | 250 | |
| BCV62B | | | 220 | | 475 | |
| BCV62C | | | 420 | | 800 | |

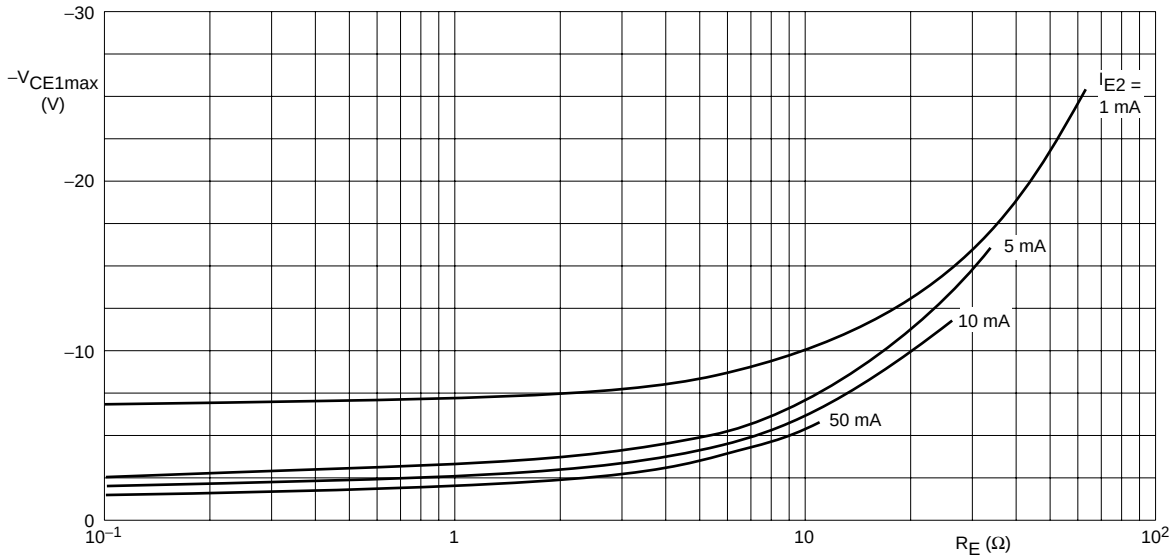
* pulse test: Pulse Width ≤300μs, Duty Cycle≤ 2.0%.

## ■ Marking

| TYPE | BCV61 | BCV61A | BCV61B | BCV61C |
|---|---|---|---|---|
| Marking | 3MP | 3JP | 3KP | 3LP |

# BCV62

## ■ Typical Characteristics




$\frac{I_{C1}}{I_{E2}}$ = 1.3 (see Fig.3).

Fig.1 Maximum collector-emitter voltage as a function of emitter resistance.